DSC5A01

Silicon NPN epitaxial planar type

For low frequency amplification DSC2A01 in SMini3 type package

■ Features

- High forward current transfer ratio h_{FE} with excellent linearity
- \bullet Low collector-emitter saturation voltage $V_{\text{CE}(\text{sat})}$
- Halogen-free / RoHS compliant
 (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

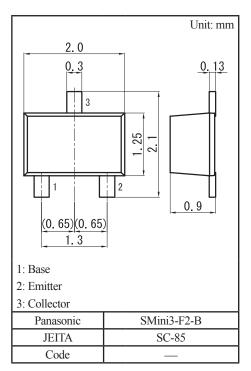
■ Marking Symbol: C8

■ Packaging

DSC5A01×0L Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

\blacksquare Absolute Maximum Ratings $\rm \,T_a \!=\! 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	50	V
Collector-emitter voltage (Base open)	V _{CEO}	40	V
Emitter-base voltage (Collector open)	V _{EBO}	15	V
Collector current	I_{C}	50	mA
Peak collector current	I _{CP}	100	mA
Collector power dissipation	P _C	150	mW
Junction temperature	T_j	150	°C
Operating ambient temperature	T _{opr}	-40 to +85	°C
Storage temperature	T _{stg}	-55 to +150	°C



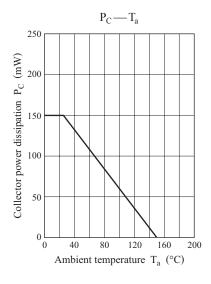
■ Electrical Characteristics $T_a = 25$ °C±3°C

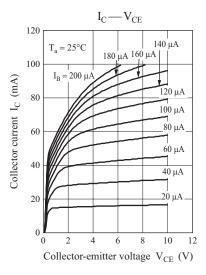
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10 \mu A, I_E = 0$	50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	40			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu A, I_C = 0$	15			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 20 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 20 \text{ V}, I_{B} = 0$			1	μΑ
Forward current transfer ratio *1	h _{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	400		2000	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1 \text{ mA}$		0.05	0.20	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$		150		MHz

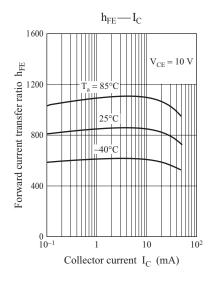
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

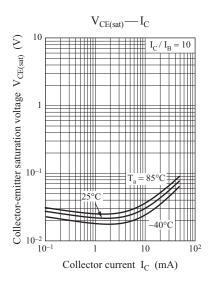
2. *1: Rank classification

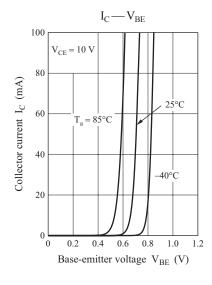
Code	R	S	Т	
Rank	R	S	Т	
h_{FE}	400 to 800	600 to 1200	1000 to 2000	
Marking Symbol	C8R	C8S	C8T	

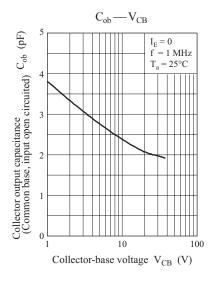


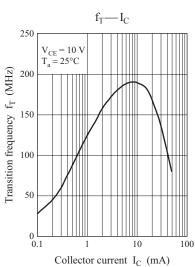








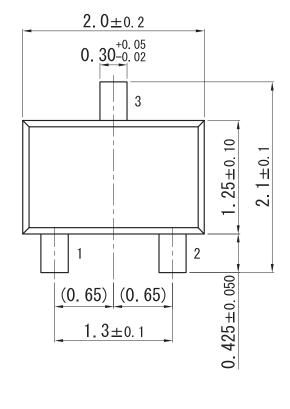


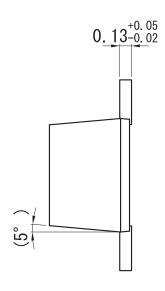


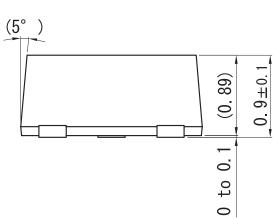
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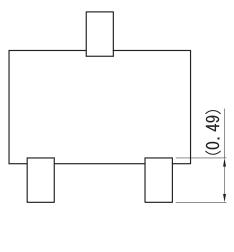
SMini3-F2-B

Unit: mm

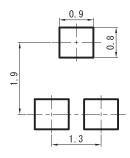








■ Land Pattern (Reference) (Unit: mm)



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